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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-WFQFN Exposed Pad
Supplier Device Package	48-HWQFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100gadna-w0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

(6/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
48 pins	48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)	Mounted	А	R5F100GAANA#U0, R5F100GCANA#U0, R5F100GDANA#U0, R5F100GEANA#U0, R5F100GFANA#U0, R5F100GGANA#U0, R5F100GHANA#U0, R5F100GJANA#U0, R5F100GKANA#U0,
				R5F100GLANA#U0
				R5F100GAANA#W0, R5F100GCANA#W0,
				R5F100GDANA#W0, R5F100GEANA#W0,
				R5F100GFANA#W0, R5F100GGANA#W0,
				R5F100GHANA#W0, R5F100GJANA#W0,
				R5F100GKANA#W0, R5F100GLANA#W0
			D	R5F100GADNA#U0, R5F100GCDNA#U0, R5F100GDDNA#U0,
				R5F100GEDNA#U0, R5F100GFDNA#U0, R5F100GGDNA#U0,
				R5F100GHDNA#U0, R5F100GJDNA#U0, R5F100GKDNA#U0,
				R5F100GLDNA#U0
				R5F100GADNA#W0, R5F100GCDNA#W0,
				R5F100GDDNA#W0, R5F100GEDNA#W0, R5F100GFDNA#W0, R5F100GGDNA#W0,
				R5F100GHDNA#W0, R5F100GJDNA#W0,
				R5F100GKDNA#W0, R5F100GLDNA#W0
			G	R5F100GAGNA#U0, R5F100GCGNA#U0, R5F100GDGNA#U0,
				R5F100GEGNA#U0, R5F100GFGNA#U0, R5F100GGGNA#U0,
				R5F100GHGNA#U0, R5F100GJGNA#U0
				R5F100GAGNA#W0, R5F100GCGNA#W0,
				R5F100GDGNA#W0, R5F100GEGNA#W0,
				R5F100GFGNA#W0, R5F100GGGNA#W0,
				R5F100GHGNA#W0, R5F100GJGNA#W0
		Not	Α	R5F101GAANA#U0, R5F101GCANA#U0, R5F101GDANA#U0,
		mounted		R5F101GEANA#U0, R5F101GFANA#U0, R5F101GGANA#U0,
				R5F101GHANA#U0, R5F101GJANA#U0, R5F101GKANA#U0,
				R5F101GLANA#U0
				R5F101GAANA#W0, R5F101GCANA#W0,
				R5F101GDANA#W0, R5F101GEANA#W0,
				R5F101GFANA#W0, R5F101GGANA#W0,
				R5F101GHANA#W0, R5F101GJANA#W0,
				R5F101GKANA#W0, R5F101GLANA#W0
			D	R5F101GADNA#U0, R5F101GCDNA#U0, R5F101GDDNA#U0,
				R5F101GEDNA#U0, R5F101GFDNA#U0, R5F101GGDNA#U0,
				R5F101GHDNA#U0, R5F101GJDNA#U0, R5F101GKDNA#U0,
				R5F101GLDNA#U0
				R5F101GADNA#W0, R5F101GCDNA#W0,
				R5F101GDDNA#W0, R5F101GEDNA#W0,
				R5F101GFDNA#W0, R5F101GGDNA#W0,
				R5F101GHDNA#W0, R5F101GJDNA#W0,
				R5F101GKDNA#W0, R5F101GLDNA#W0

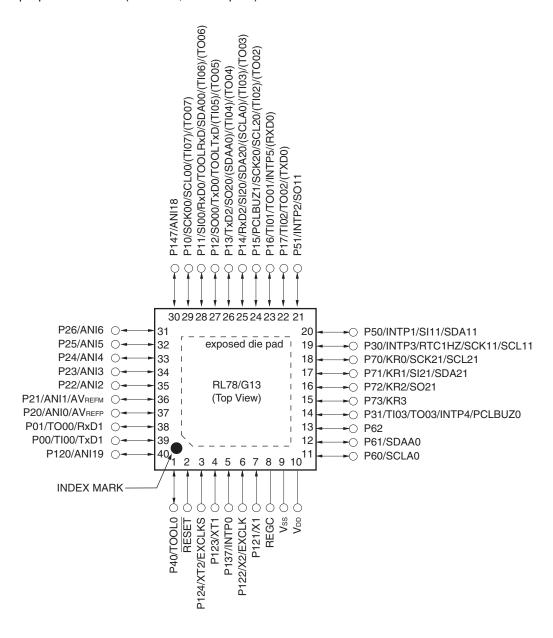
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



### 1.3.7 40-pin products

• 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



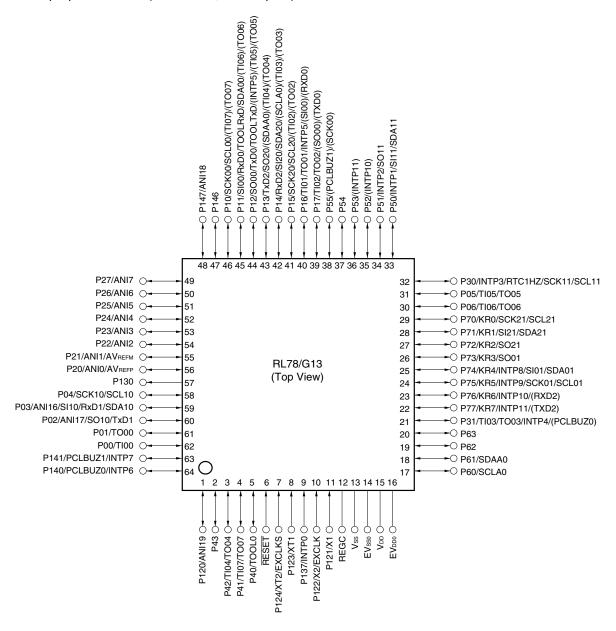
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to Vss.

### 1.3.11 64-pin products

- 64-pin plastic LQFP (12 x 12 mm, 0.65 mm pitch)
- 64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)

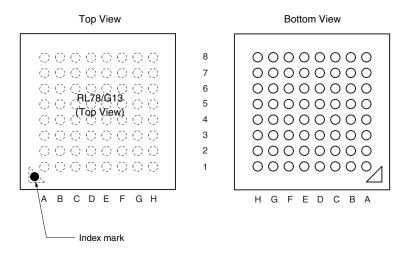


- Cautions 1. Make EVsso pin the same potential as Vss pin.
  - 2. Make VDD pin the potential that is higher than EVDDO pin.
  - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).

#### Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V<sub>DD</sub> and EV<sub>DD0</sub> pins and connect the Vss and EV<sub>SS0</sub> pins to separate ground lines.
- **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.

• 64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)



Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A1	P05/TI05/TO05	C1	P51/INTP2/SO11	E1	P13/TxD2/SO20/ (SDAA0)/(TI04)/(TO04)	G1	P146
A2	P30/INTP3/RTC1HZ /SCK11/SCL11	C2	P71/KR1/SI21/SDA21	E2	P14/RxD2/SI20/SDA20 /(SCLA0)/(TI03)/(TO03)	-	P25/ANI5
A3	P70/KR0/SCK21 /SCL21	СЗ	P74/KR4/INTP8/SI01 /SDA01	E3	P15/SCK20/SCL20/ (TI02)/(TO02)	G3	P24/ANI4
A4	P75/KR5/INTP9 /SCK01/SCL01	C4	P52/(INTP10)	E4	P16/TI01/TO01/INTP5 /(SI00)/(RxD0)	G4	P22/ANI2
A5	P77/KR7/INTP11/ (TxD2)	C5	P53/(INTP11)	E5	P03/ANI16/SI10/RxD1 /SDA10	G5	P130
A6	P61/SDAA0	C6	P63	E6	P41/TI07/TO07	G6	P02/ANI17/SO10/TxD1
A7	P60/SCLA0	C7	Vss	E7	RESET	G7	P00/TI00
A8	EV <sub>DD0</sub>	C8	P121/X1	E8	P137/INTP0	G8	P124/XT2/EXCLKS
B1	P50/INTP1/SI11 /SDA11	D1	P55/(PCLBUZ1)/ (SCK00)	F1	P10/SCK00/SCL00/ (TI07)/(TO07)	H1	P147/ANI18
B2	P72/KR2/SO21	D2	P06/TI06/TO06	F2	P11/SI00/RxD0 /TOOLRxD/SDA00/ (TI06)/(TO06)	H2	P27/ANI7
В3	P73/KR3/SO01	D3	P17/TI02/TO02/ (SO00)/(TxD0)	F3	P12/SO00/TxD0 /TOOLTxD/(INTP5)/ (TI05)/(TO05)	НЗ	P26/ANI6
B4	P76/KR6/INTP10/ (RxD2)	D4	P54	F4	P21/ANI1/AVREFM	H4	P23/ANI3
B5	P31/TI03/TO03 /INTP4/(PCLBUZ0)	D5	P42/TI04/TO04	F5	P04/SCK10/SCL10	H5	P20/ANI0/AVREFP
B6	P62	D6	P40/TOOL0	F6	P43	H6	P141/PCLBUZ1/INTP7
B7	V <sub>DD</sub>	D7	REGC	F7	P01/TO00	H7	P140/PCLBUZ0/INTP6
B8	EVsso	D8	P122/X2/EXCLK	F8	P123/XT1	H8	P120/ANI19

Cautions 1. Make EVsso pin the same potential as Vss pin.

- 2. Make  $V_{\text{DD}}$  pin the potential that is higher than  $\text{EV}_{\text{DD0}}$  pin.
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).

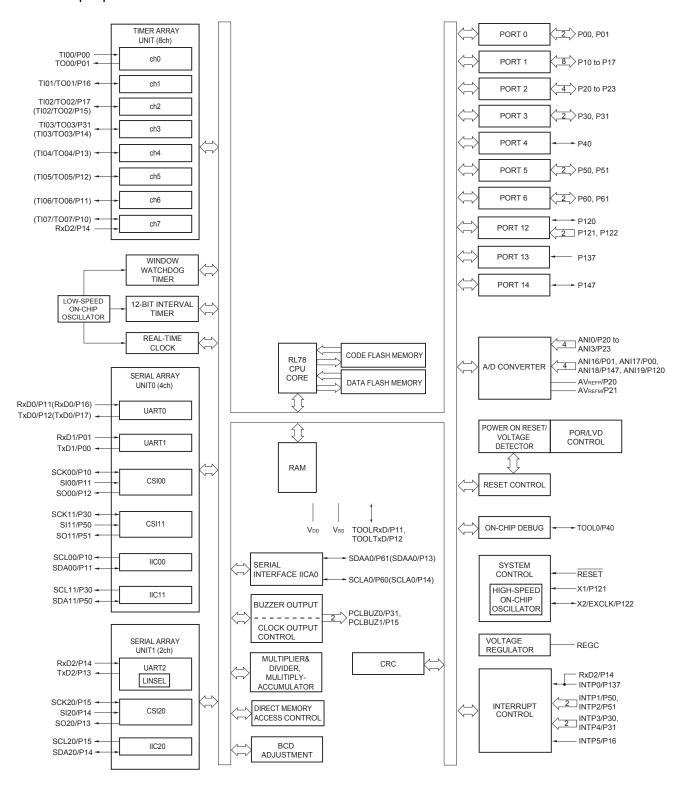
Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V<sub>DD</sub> and EV<sub>DD0</sub> pins and connect the Vss and EV<sub>SS0</sub> pins to separate ground lines.
- **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.

#### 1.4 Pin Identification

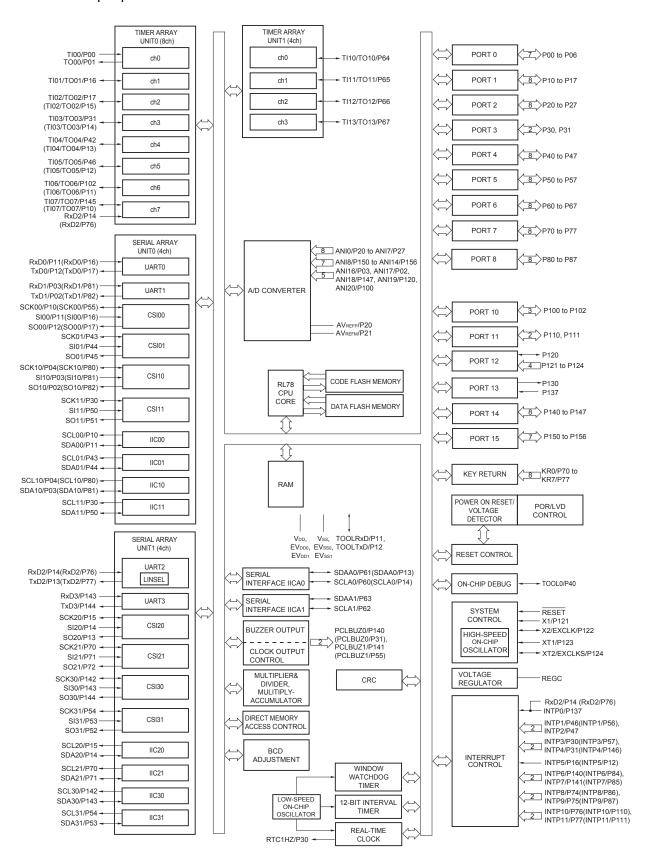
ANI0 to ANI14, REGC: Regulator capacitance RESET: ANI16 to ANI26: Reset Analog input AVREFM: A/D converter reference RTC1HZ: Real-time clock correction clock potential (- side) input (1 Hz) output AVREFP: A/D converter reference RxD0 to RxD3: Receive data potential (+ side) input SCK00, SCK01, SCK10, EVDD0, EVDD1: Power supply for port SCK11, SCK20, SCK21, EVsso, EVss1: Ground for port SCLA0, SCLA1: Serial clock input/output EXCLK: External clock input (Main SCLA0, SCLA1, SCL00, SCL01, SCL10, SCL11, system clock) **EXCLKS**: External clock input SCL20, SCL21, SCL30, (Subsystem clock) SCL31: Serial clock output INTP0 to INTP11: Interrupt request from SDAA0, SDAA1, SDA00, peripheral SDA01, SDA10, SDA11, KR0 to KR7: Key return SDA20,SDA21, SDA30, P00 to P07: Port 0 SDA31: Serial data input/output P10 to P17: Port 1 SI00, SI01, SI10, SI11, P20 to P27: Port 2 SI20, SI21, SI30, SI31: Serial data input P30 to P37: Port 3 SO00, SO01, SO10, P40 to P47: Port 4 SO11, SO20, SO21, P50 to P57: Port 5 SO30, SO31: Serial data output P60 to P67: Port 6 TI00 to TI07, P70 to P77: Port 7 TI10 to TI17: Timer input P80 to P87: Port 8 TO00 to TO07. P90 to P97: Port 9 TO10 to TO17: Timer output P100 to P106: Port 10 TOOL0: Data input/output for tool P110 to P117: Port 11 TOOLRxD, TOOLTxD: Data input/output for external device P120 to P127: Port 12 TxD0 to TxD3: Transmit data P130, P137: Port 13 V<sub>DD</sub>: Power supply P140 to P147: Port 14 Vss: Ground P150 to P156: Port 15 X1, X2: Crystal oscillator (main system clock) PCLBUZ0, PCLBUZ1: Programmable clock XT1, XT2: Crystal oscillator (subsystem clock) output/buzzer output

# 1.5.4 30-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

# 1.5.13 100-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

[40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]

# Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

	Item	40	pin	4.4	-pin	40	·pin	F0	nin		·pin
	nem		<u> </u>	44	i			52-	-pin I		İ
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
		100	101	100	101	100	101	100	101	100	101
		Ex	Ex	×	×	χ Ω	ωx	×	×	Ž	Ž
Code flash me	emory (KB)	16 to	o 192	16 t	o 512	16 t	512	32 to	o 512	32 to	o 512
Data flash me	mory (KB)	4 to 8	-	4 to 8	_	4 to 8	-	4 to 8	_	4 to 8	_
RAM (KB)		2 to 1	16 <sup>Note1</sup>	2 to :	32 <sup>Note1</sup>	2 to 3	32 <sup>Note1</sup>	2 to 3	32 <sup>Note1</sup>	2 to 3	32 <sup>Note1</sup>
Address space	e	1 MB									
Main system clock	High-speed system clock	HS (High HS (High LS (Low-	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V <sub>DD</sub> = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V <sub>DD</sub> = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V <sub>DD</sub> = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V <sub>DD</sub> = 1.6 to 5.5 V)								
	High-speed on-chip oscillator	HS (High LS (Low-	HS (High-speed main) mode: 1 to 32 MHz ( $V_{DD}$ = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ( $V_{DD}$ = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ( $V_{DD}$ = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ( $V_{DD}$ = 1.6 to 5.5 V)								
Subsystem cl	ock	XT1 (crys 32.768 k		ation, exte	ernal subsy	stem cloc	k input (E	XCLKS)			
Low-speed or	15 kHz (TYP.)										
General-purp	ose registers	(8-bit reg	ister × 8)	× 4 banks							
Minimum insti	ruction execution time	0.03125 $μ$ s (High-speed on-chip oscillator: f <sub>IH</sub> = 32 MHz operation)									
		0.05 μs (	High-spee	ed system	clock: fmx	= 20 MHz	operation	)			
		30.5 $\mu$ s (Subsystem clock: fsub = 32.768 kHz operation)									
Instruction se	t	<ul> <li>Data transfer (8/16 bits)</li> <li>Adder and subtractor/logical operation (8/16 bits)</li> <li>Multiplication (8 bits × 8 bits)</li> <li>Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.</li> </ul>									
I/O port	Total	3	36	4	40	2	14	4	18	5	58
	CMOS I/O	(N-ch (	28 O.D. I/O ithstand ge]: 10)	(N-ch [V <sub>DD</sub> w	31 O.D. I/O rithstand ge]: 10)	(N-ch (	34 O.D. I/O ithstand je]: 11)	(N-ch (	38 O.D. I/O ithstand ge]: 13)	(N-ch (	18 O.D. I/O ithstand ge]: 15)
	CMOS input		5		5		5		5		5
	CMOS output		=		=		1		1		1
	N-ch O.D. I/O (withstand voltage: 6 V)		3		4		4		4		4
Timer	16-bit timer					8 cha	nnels				
	Watchdog timer					1 cha	annel				
	Real-time clock (RTC)					1 cha	annel				
	12-bit interval timer (IT)	` '									
	Timer output	4 channels (PWM outputs: 4 Note 2), outputs: 3 Note 2), 8 channels (PWM outputs: 7 Note 2) Note 3 outputs: 7 Note 2) Note 3 outputs: 7 Note 2) Note 3									
	RTC output	1 channe • 1 Hz (s		ı clock: fsu	ıв = 32.768	3 kHz)					

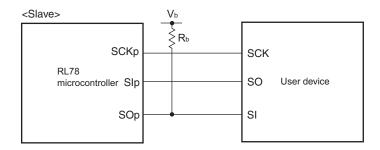
Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = E to G, J, L): Start address FF300H R5F100xE, R5F101xE (x = E to G, J, L): Start address FEF00H R5F100xJ, R5F101xJ (x = F, G, J, L): Start address F7F00H Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

### CSI mode connection diagram (during communication at different potential)



- Remarks 1.  $R_b[\Omega]$ :Communication line (SOp) pull-up resistance,  $C_b[F]$ : Communication line (SOp) load capacitance,  $V_b[V]$ : Communication line voltage
  - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
  - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
  - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

### (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I<sup>2</sup>C mode) (2/2)

(Ta = -40 to +85°C, 1.8 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (high main)	•	,	/-speed Mode	LV (low main)	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1/fмск + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	1/fмск + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	1/fmck + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$\label{eq:substitute} \begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/fmck + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ &1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ &C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{aligned} $	1/fмск + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
Data hold time (transmission)	thd:dat	$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	0	355	0	355	0	355	ns
		$\label{eq:section} \begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	0	355	0	355	0	355	ns
		$\begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	0	405	0	405	0	405	ns

**Notes 1.** The value must also be equal to or less than  $f_{MCK}/4$ .

- 2. Use it with  $EV_{DD0} \ge V_b$ .
- 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{\text{DD}}, \text{Reference voltage (-)} = \text{V}_{\text{SS}})$ 

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$		1.2	±7.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI0 to ANI14,	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
		ANI16 to ANI26	$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μS
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
			$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μS
Zero-scale error <sup>Notes 1, 2</sup>	Ezs	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
			$\begin{array}{c} \text{1.6 V} \leq \text{VDD} \leq 5.5 \text{ V} \\ \text{Note 3} \end{array}$			±0.85	%FSR
Full-scale error <sup>Notes 1, 2</sup>	E <sub>F</sub> S	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
			$\begin{array}{ c c c }\hline 1.6 \ V \leq V_{DD} \leq 5.5 \ V\\ & \text{Note 3} \end{array}$			±0.85	%FSR
Integral linearity error <sup>Note 1</sup>	ILE	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±4.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±6.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
			$1.6~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$ Note 3			±2.5	LSB
Analog input voltage	Vain	ANI0 to ANI14		0		V <sub>DD</sub>	٧
		ANI16 to ANI26		0		EV <sub>DD0</sub>	٧
		Internal reference voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (hi		VBGR Note 4		V	
		Temperature sensor output (2.4 V ≤ VDD ≤ 5.5 V, HS (hi	-	V <sub>TMPS25</sub> Note 4			V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When the conversion time is set to 57  $\mu$ s (min.) and 95  $\mu$ s (max.).
- 4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

#### 3.3 DC Characteristics

#### 3.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$ 

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high <sup>Note 1</sup>	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V			-3.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			-30.0	mA
		P125 to P127, P130, P140 to P145	$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V}$			-10.0	mA
			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			-5.0	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty $\leq$ 70% Note 3)				-30.0	mA
			$2.7~V \leq EV_{DD0} < 4.0~V$			-19.0	mA
			2.4 V ≤ EVDD0 < 2.7 V			-10.0	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$ )	$2.4~V \le EV_{DD0} \le 5.5~V$			-60.0	mA
	Іон2	Per pin for P20 to P27, P150 to P156	$2,4~V \leq V_{DD} \leq 5.5~V$			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% <sup>Note 3</sup> )	$2.4~V \leq V_{DD} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV<sub>DD0</sub>, EV<sub>DD1</sub>, V<sub>DD</sub> pins to an output pin.
  - 2. Do not exceed the total current value.
  - **3.** Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins =  $(IOH \times 0.7)/(n \times 0.01)$ 

<Example> Where n = 80% and  $I_{OH} = -10.0$  mA

Total output current of pins =  $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$  mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

# (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (Ta = -40 to $+105^{\circ}$ C, 2.4 V $\leq$ EV<sub>DD0</sub> = EV<sub>DD1</sub> $\leq$ V<sub>DD</sub> $\leq$ 5.5 V, Vss = EV<sub>SS0</sub> = EV<sub>SS1</sub> = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I <sub>DD2</sub>	HALT	HS (high-	fih = 32 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.62	3.40	mA
Current Note 1	Note 2	mode	speed main) mode Note 7		V <sub>DD</sub> = 3.0 V		0.62	3.40	mA
			mode	fin = 24 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.50	2.70	mA
				V <sub>DD</sub> = 3.0 V		0.50	2.70	mA	
				fiн = 16 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.44	1.90	mA
					V <sub>DD</sub> = 3.0 V		0.44	1.90	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	2.10	mA
			speed main) mode Note 7	V <sub>DD</sub> = 5.0 V	Resonator connection		0.48	2.20	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	2.10	mA
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.48	2.20	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA
				V <sub>DD</sub> = 5.0 V	Resonator connection		0.28	1.20	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA
			V <sub>DD</sub> = 3.0 V	Resonator connection		0.28	1.20	mA	
		Subsystem	fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.28	0.61	μΑ	
			clock operation	T <sub>A</sub> = -40°C	Resonator connection		0.47	0.80	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.34	0.61	μΑ
				T <sub>A</sub> = +25°C	Resonator connection		0.53	0.80	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.41	2.30	μΑ
				T <sub>A</sub> = +50°C	Resonator connection		0.60	2.49	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.64	4.03	μΑ
				T <sub>A</sub> = +70°C	Resonator connection		0.83	4.22	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		1.09	8.04	μΑ
				T <sub>A</sub> = +85°C	Resonator connection		1.28	8.23	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		5.50	41.00	μΑ
				T <sub>A</sub> = +105°C	Resonator connection		5.50	41.00	μΑ
	IDD3 <sup>Note 6</sup>	STOP	T <sub>A</sub> = -40°C			0.19	0.52	μΑ	
		mode <sup>Note 8</sup>	T <sub>A</sub> = +25°C				0.25	0.52	μΑ
			T <sub>A</sub> = +50°C				0.32	2.21	μΑ
			T <sub>A</sub> = +70°C				0.55	3.94	μΑ
			T <sub>A</sub> = +85°C				1.00	7.95	μΑ
			T <sub>A</sub> = +105°C				5.00	40.00	μΑ

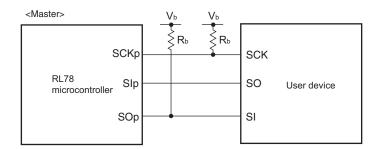
(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
  - 2. During HALT instruction execution by flash memory.
  - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
  - 4. When high-speed system clock and subsystem clock are stopped.
  - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
  - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
  - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$  to 32 MHz  $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$  to 16 MHz

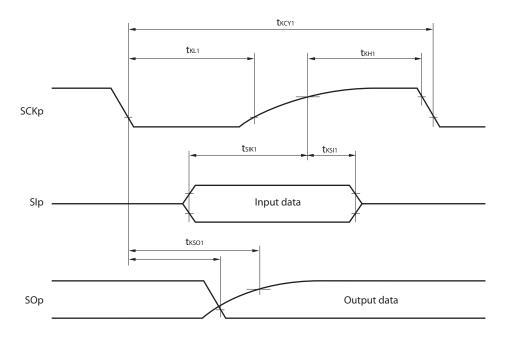
- 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
  - 2. fin: High-speed on-chip oscillator clock frequency
  - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
  - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is  $T_A = 25^{\circ}C$

#### CSI mode connection diagram (during communication at different potential)

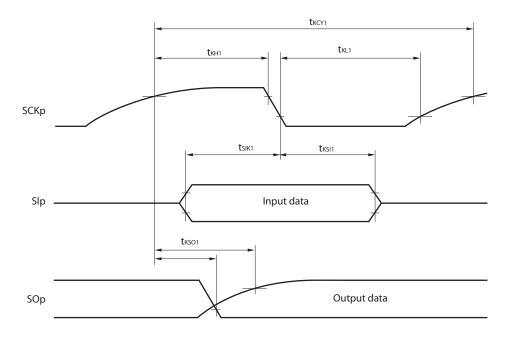


- Remarks 1.  $R_b[\Omega]$ :Communication line (SCKp, SOp) pull-up resistance,  $C_b[F]$ : Communication line (SCKp, SOp) load capacitance,  $V_b[V]$ : Communication line voltage
  - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
  - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
  - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

# CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



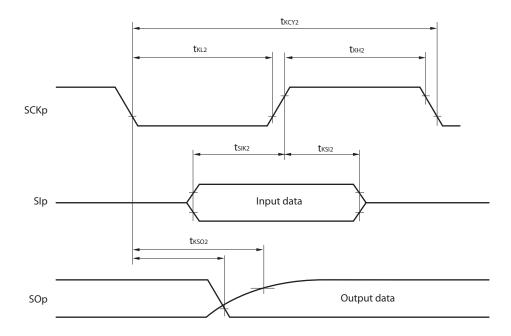
# CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



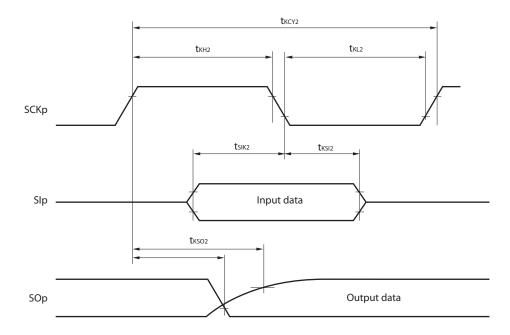
**Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 00, 01, 02, 10, 12, 13), n: Channel number (n = 0, 2), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

**2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

# CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



# CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

**2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

#### 3.5.2 Serial interface IICA

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	HS (h	(high-speed main) Mode			Unit
				Standard Fast Mod Mode		Mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fclk ≥ 3.5 MHz	-	_	0	400	kHz
		Standard mode: fclk ≥ 1 MHz	0	100	-	-	kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μS
Hold time <sup>Note 1</sup>	thd:sta		4.0		0.6		μS
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μS
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μS
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μS
Setup time of stop condition	tsu:sto		4.0		0.6		μS
Bus-free time	<b>t</b> BUF		4.7		1.3		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

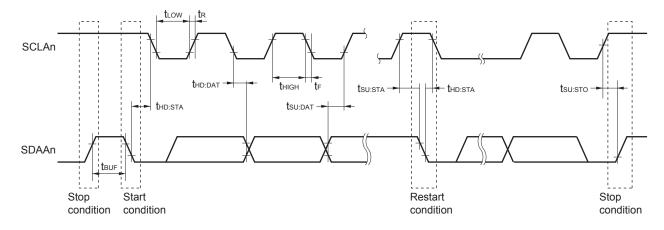
2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

**Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode:  $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode:  $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$ 

#### **IICA** serial transfer timing



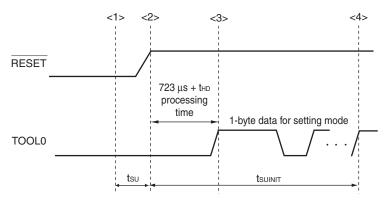
Remark n = 0, 1

<R>

### 3.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)		POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

**Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

 $t_{\text{SU}}$ : Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

			Description
Rev.	Date	Page	Summary
3.00	Aug 02, 2013	118	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		118	Modification of table and note in 2.6.3 POR circuit characteristics
		119	Modification of table in 2.6.4 LVD circuit characteristics
		120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		120	Renamed to 2.6.5 Power supply voltage rising slope characteristics
		122	Modification of table, figure, and remark in 2.10 Timing Specs for Switching Flash Memory Programming Modes
		123	Modification of caution 1 and description
		124	Modification of table and remark 3 in Absolute Maximum Ratings (T <sub>A</sub> = 25°C)
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics
		126	Modification of table in 3.2.2 On-chip oscillator characteristics
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)
		133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (2/2)
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2)
		139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)
		140	Modification of (3) Peripheral Functions (Common to all products)
		142	Modification of table in 3.4 AC Characteristics
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		143	Modification of figure of AC Timing Test Points
		143	Modification of figure of External System Clock Timing
		145	Modification of figure of AC Timing Test Points
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)
		146	Modification of description in (2) During communication at same potential (CSI mode)
		147	Modification of description in (3) During communication at same potential (CSI mode)
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I <sup>2</sup> C mode)
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)